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# 2SC2619

Silicon NPN Epitaxial

# HITACHI

ADE-208-1070 (Z)  
1st. Edition  
Mar. 2001

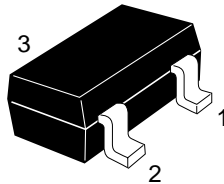
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## Application

High frequency amplifier

## Outline

MPAK



1. Emitter
2. Base
3. Collector

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	30	V
Collector to emitter voltage	$V_{CEO}$	30	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

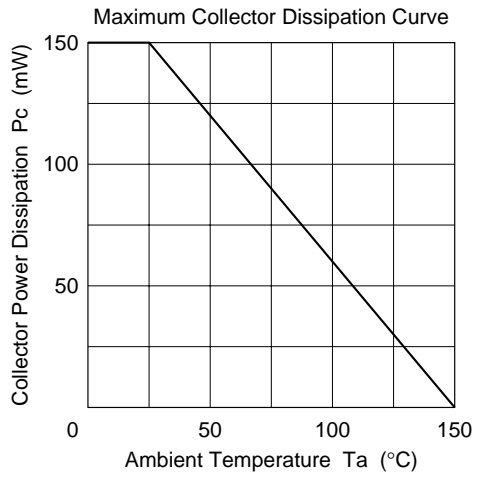
## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 20 \text{ V}, I_C = 0$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	35	—	200		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Gain bandwidth product	$f_T$	—	230	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	—	3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Noise figure	NF	—	5.0	—	dB	$V_{CE} = 6 \text{ V}, I_C = 2 \text{ mA}, f = 1 \text{ MHz}, R_g = 500 \Omega$

Note: 1. The 2SC2619 is grouped by  $h_{FE}$  as follows.

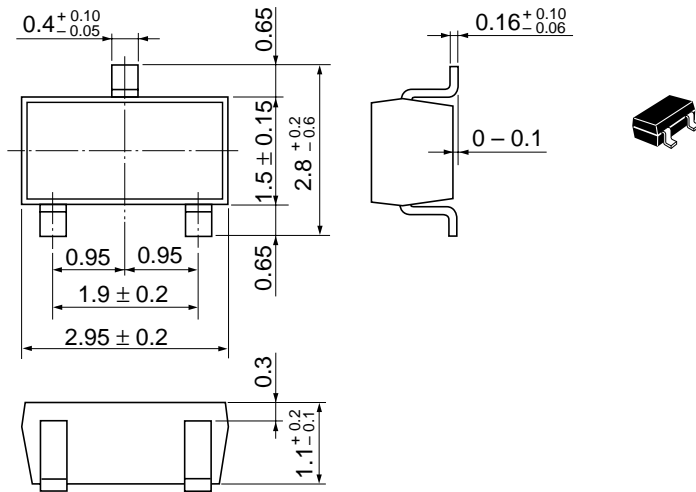
Grade	A	B	C
Mark	FA	FB	FC
$h_{FE}$	35 to 75	60 to 120	100 to 200

See characteristic curves of 2SC460.



**Package Dimensions**

As of January, 2001  
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

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